

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0030], with the following rewritten paragraph:

-- FIG. 3 provides a pictorial representation of the initial or starting semiconductor substrate (labeled as 5) that is employed in the present invention. FIG. 3 includes the $\langle 001 \rangle$ direction and the $\langle 110 \rangle$ direction of current flow. The $\langle 100 \rangle$ direction of current flow is perpendicular to both the $\langle 001 \rangle$ and the $\langle 110 \rangle$; hence the $\langle 100 \rangle$ direction is coming out of the plane of the drawing. The term "semiconductor substrate" is used in the present invention to denote any semiconducting material including, but not limited to: Si, SiGe, SiC, or SiGeC, GaAs, InAs, InP or other like III/V compound semiconductors. A preferred semiconductor substrate is a Si substrate.--